

Part Number: SA04-11SEKWA

Super Bright Orange

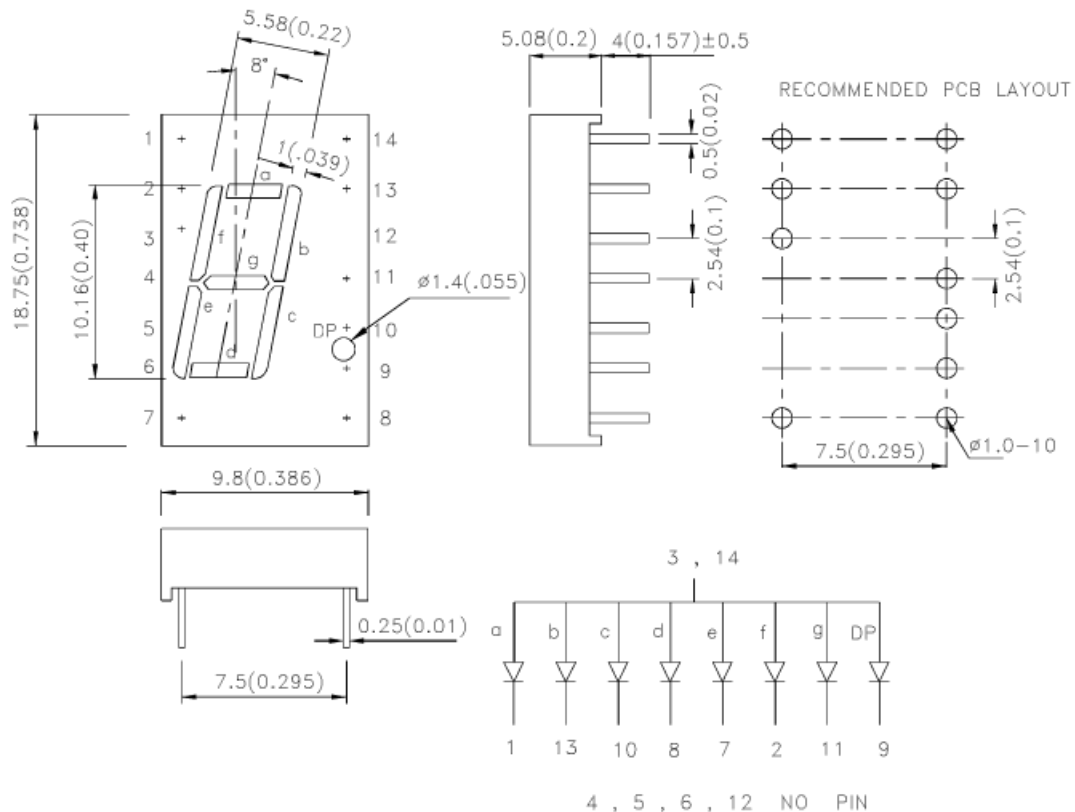
### Features

- 0.4 inch digit height.
- Low current operation.
- Excellent character appearance.
- Easy mounting on P.C. boards or sockets.
- Mechanically rugged.
- Standard : gray face, white segment.
- RoHS compliant.

### Description

The Super Bright Orange device is made with AlGaInP (on GaAs substrate) light emitting diode chip.

### Package Dimensions & Internal Circuit Diagram



#### Notes:

1. All dimensions are in millimeters (inches), Tolerance is  $\pm 0.25(0.01)$  unless otherwise noted.
2. The specifications, characteristics and technical data described in the datasheet are subject to change without prior notice.



## Selection Guide

Part No.	Dice	Lens Type	Iv (ucd) [1] @ 10mA		Description
			Min.	Typ.	
SA04-11SEKWA	Super Bright Orange (AlGaInP)	White Diffused	52000	160000	Common Anode, Rt. Hand Decimal.

Note:

1. Luminous intensity/ luminous Flux: +/-15%.

## Electrical / Optical Characteristics at TA=25°C

Symbol	Parameter	Device	Typ.	Max.	Units	Test Conditions
$\lambda_{peak}$	Peak Wavelength	Super Bright Orange	610		nm	I <sub>F</sub> =20mA
$\lambda_D$ [1]	Dominant Wavelength	Super Bright Orange	601		nm	I <sub>F</sub> =20mA
$\Delta\lambda_{1/2}$	Spectral Line Half-width	Super Bright Orange	29		nm	I <sub>F</sub> =20mA
C	Capacitance	Super Bright Orange	15		pF	V <sub>F</sub> =0V;f=1MHz
V <sub>F</sub> [2]	Forward Voltage	Super Bright Orange	2.1	2.5	V	I <sub>F</sub> =20mA
I <sub>R</sub>	Reverse Current	Super Bright Orange		10	uA	V <sub>R</sub> =5V

Notes:

1. Wavelength: +/-1nm.

2. Forward Voltage: +/-0.1V.

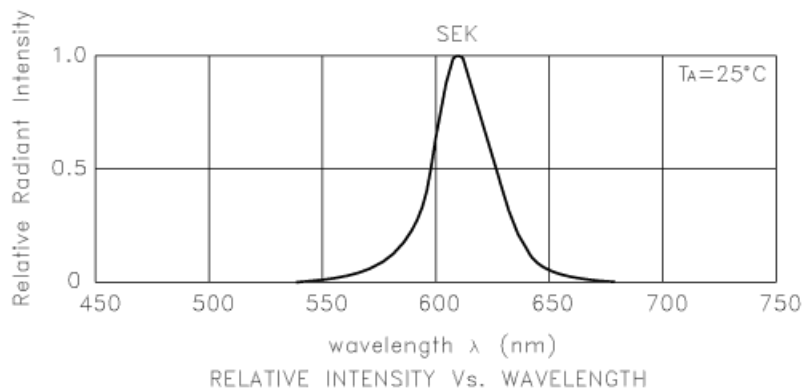
## Absolute Maximum Ratings at TA=25°C

Parameter	Super Bright Orange	Units
Power dissipation	75	mW
DC Forward Current	30	mA
Peak Forward Current [1]	195	mA
Reverse Voltage	5	V
Operating / Storage Temperature	-40°C To +85°C	
Lead Solder Temperature[2]	260°C For 3-5 Seconds	

Notes:

1. 1/10 Duty Cycle, 0.1ms Pulse Width.

2. 2mm below package base.



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